## 256K x 8 Static RAM Module

## Features

- High-density 2-megabit SRAM module
- High-speed CMOS SRAMs
- Access time of 20 ns
- Low active power
-5.3W (max.)
- SMD technology
- Separate data I/O
- 60-pin ZIP package
- TTL-compatible inputs and outputs
- Low profile
—Max. height of 0.5 in .
- Small PCB footprint
-1.14 sq. in.


## Functional Description

The CYM1441 is a very high performance 2-megabit static RAM module organized as 256 K words by 8 bits. The module is constructed using eight $256 \mathrm{~K} \times 1$ static RAMs in SOJ packages mounted onto an epoxy laminate substrate with pins. Two chip selects ( $\overline{C S}_{L}$ and $\overline{C S}_{U}$ ) are used to independently enable the upper and lower 4 bits of the data word. Writing to the memory module is accomplished when the chip select ( $\overline{\mathrm{CS}}$ ) and write enable ( $\overline{\mathrm{WE}}$ ) inputs are both LOW. Data on the eight input pins ( $\mathrm{DI}_{0}$ through $\mathrm{DI}_{7}$ ) is written into the memory location specified on the address pins ( $\mathrm{A}_{0}$ through $\left.\mathrm{A}_{17}\right)$. Reading the device is accomplished by taking chip select (CS) LOW while write enable (WE) remains inactive or HIGH. Under these conditions, the contents of the memory location specified on the address pins will appear on the appropriate data output pins $\left(\mathrm{DO}_{0}\right.$ through $\left.\mathrm{DO}_{7}\right)$. The data output pins remain in a highimpedance state unless the module is selected and write enable ( $\overline{\mathrm{WE}}$ ) is HIGH. Two pins ( $\mathrm{PD}_{0}$ and $\mathrm{PD}_{1}$ ) are used to identify module memory density in applications where alternate versions of the JEDEC-standard modules can be interchanged.

## Logic Block Diagram



Pin Configuration ZIP


## Selection Guide

|  | $\mathbf{1 4 4 1 - 2 0}$ | $\mathbf{1 4 4 1 - 2 5}$ | $\mathbf{1 4 4 1 - 3 5}$ | $\mathbf{1 4 4 1 - 4 5}$ |
| :--- | :---: | :---: | :---: | :---: |
| Maximum Access Time (ns) | 20 | 25 | 35 | 45 |
| Maximum Operating Current (mA) | 960 | 960 | 960 | 960 |
| Maximum Standby Current (mA) | 320 | 320 | 320 | 320 |

Shaded area contains preliminary information.

## Maximum Ratings

(Above which the useful life may be impaired.)
Storage Temperature $\qquad$ $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$
Ambient Temperature with
Power Applied. $\qquad$
Supply Voltage to Ground Potential $\qquad$ $-10^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ .-0.5 V to +7.0 V

DC Voltage Applied to Outputs
in High Z State............................................ 0.5 V to +7.0 V
DC Input Voltage
-0.5 V to +7.0 V
Operating Range

| Range | Ambient <br> Temperature | V $_{\text {CC }}$ |
| :---: | :---: | :---: |
| Commercial | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | $5 \mathrm{~V} \pm 10 \%$ |

Electrical Characteristics Over the Operating Range

| Parameter | Description | Test Conditions | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage | $\mathrm{V}_{\mathrm{CC}}=\mathrm{Min} ., \mathrm{I}_{\mathrm{OH}}=-4.0 \mathrm{~mA}$ | 2.4 |  | V |
| $\mathrm{V}_{\mathrm{OL}}$ | Output LOW Voltage | $\mathrm{V}_{\mathrm{CC}}=\mathrm{Min} ., \mathrm{I}_{\mathrm{OL}}=12.0 \mathrm{~mA}$ |  | 0.4 | V |
| $\mathrm{V}_{\text {IH }}$ | Input HIGH Voltage |  | 2.2 | $\mathrm{V}_{\mathrm{CC}}$ | V |
| $\mathrm{V}_{\text {IL }}$ | Input LOW Voltage ${ }^{[1]}$ |  | -0.5 | 0.8 | V |
| $\mathrm{I}_{\mathrm{IX}}$ | Input Load Current | $\mathrm{GND} \leq \mathrm{V}_{\mathrm{I}} \leq \mathrm{V}_{\mathrm{CC}}$ | -80 | +80 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{Oz}}$ | Output Leakage Current | $\mathrm{GND} \leq \mathrm{V}_{\mathrm{O}} \leq \mathrm{V}_{\mathrm{CC}}$, Output Disabled | -50 | +50 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{CC}}$ | $\mathrm{V}_{\text {CC }}$ Operating Supply Current | $\mathrm{V}_{\mathrm{CC}}=$ Max., $\mathrm{l}_{\text {OUT }}=0 \mathrm{~mA}, \overline{\mathrm{CS}} \leq \mathrm{V}_{\text {IL }}$ |  | 960 | mA |
| $\mathrm{I}_{\text {SB1 }}$ | Automatic $\overline{C S}$ Power-Down Current | $\begin{aligned} & \text { Max. } \mathrm{V}_{\mathrm{CC}}, \overline{\mathrm{CS}} \geq \mathrm{V}_{\mathrm{IH}}, \\ & \text { Min. Duty Cycle }=100 \% \end{aligned}$ |  | 320 | mA |
| $\mathrm{I}_{\text {SB2 }}$ | Automatic $\overline{\mathrm{CS}}$ <br> Power-Down Current | $\begin{aligned} & \text { Max. } \mathrm{V}_{\mathrm{CC}}, \overline{\mathrm{CS}} \geq \mathrm{V}_{\mathrm{CC}}-0.2 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{IN}} \geq \mathrm{V}_{\mathrm{CC}}-0.2 \mathrm{~V} \text { or } \mathrm{V}_{\mathrm{IN}} \leq 0.2 \mathrm{~V} \end{aligned}$ |  | 160 | mA |

## Capacitance ${ }^{[2]}$

| Parameter | Description | Test Conditions | Max. | Unit |
| :--- | :--- | :--- | :---: | :---: |
| $\mathrm{C}_{\mathrm{IN}}$ | Input Capacitance | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}, \mathrm{f}=1 \mathrm{MHz}$, | 60 | pF |
| $\mathrm{C}_{\text {OUT }}$ | Output Capacitance | $\mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V}$ | 15 | pF |

## AC Test Loads and Waveforms



Equivalent to: THÉVENIN EQUIVALENT


## Notes:

1. $\quad \mathrm{V}_{\mathrm{IN}}$ (min.) $=-3.0 \mathrm{~V}$ for pulse widths less than 20 ns .
2. Tested on a sample basis.

Switching Characteristics Over the Operating Range ${ }^{[3]}$

| Parameter | Description | 1441-20 |  | 1441-25 |  | 1441-35 |  | 1441-45 |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min. | Max. | Min. | Max. | Min. | Max. | Min. | Max. |  |
| READ CYCLE |  |  |  |  |  |  |  |  |  |  |
| $\mathrm{t}_{\mathrm{RC}}$ | Read Cycle Time | 20 |  | 25 |  | 35 |  | 45 |  | ns |
| $\mathrm{t}_{\mathrm{AA}}$ | Address to Data Valid |  | 20 |  | 25 |  | 35 |  | 45 | ns |
| $\mathrm{t}_{\text {OHA }}$ | Data Hold from Address Change | 3 |  | 3 |  | 3 |  | 3 |  | ns |
| $\mathrm{t}_{\text {ACS }}$ | $\overline{\overline{C S}}$ LOW to Data Valid |  | 20 |  | 25 |  | 35 |  | 45 | ns |
| t LZCS | $\overline{\text { CS LOW to Low Z }}$ | 3 |  | 3 |  | 3 |  | 3 |  | ns |
| $\mathrm{t}_{\mathrm{HZCS}}$ | $\overline{\mathrm{CS}}$ HIGH to High $\mathrm{Z}^{[4]}$ |  | 12 |  | 15 |  | 25 |  | 30 | ns |
| $\mathrm{t}_{\mathrm{PU}}$ | $\overline{\mathrm{CS}}$ LOW to Power-Up | 0 |  | 0 |  | 0 |  | 0 |  | ns |
| $\mathrm{t}_{\text {PD }}$ | $\overline{\mathrm{CS}}$ HIGH to Power-Down |  | 20 |  | 25 |  | 35 |  | 45 | ns |
| WRITE CYCLE ${ }^{[5]}$ |  |  |  |  |  |  |  |  |  |  |
| $\mathrm{t}_{\text {WC }}$ | Write Cycle Time | 20 |  | 25 |  | 35 |  | 45 |  | ns |
| tscs | $\overline{\mathrm{CS}}$ LOW to Write End | 15 |  | 20 |  | 30 |  | 35 |  | ns |
| $\mathrm{t}_{\text {AW }}$ | Address Set-Up to Write End | 15 |  | 20 |  | 30 |  | 35 |  | ns |
| $\mathrm{t}_{\mathrm{HA}}$ | Address Hold from Write End | 2 |  | 2 |  | 2 |  | 2 |  | ns |
| $\mathrm{t}_{\text {SA }}$ | Address Set-Up to Write Start | 0 |  | 0 |  | 0 |  | 2 |  | ns |
| tPWE | WE Pulse Width | 15 |  | 20 |  | 25 |  | 30 |  | ns |
| $\mathrm{t}_{\text {SD }}$ | Data Set-Up to Write End | 13 |  | 15 |  | 20 |  | 20 |  | ns |
| $\mathrm{t}_{\mathrm{HD}}$ | Data Hold from Write End | 0 |  | 0 |  | 0 |  | 0 |  | ns |
| tLZWE | $\overline{\text { WE HIGH to Low Z }}$ | 3 |  | 3 |  | 3 |  | 3 |  | ns |
| $\mathrm{t}_{\text {HZWE }}$ | $\overline{\mathrm{WE}}$ LOW to High $\mathrm{Z}^{[4]}$ | 0 | 13 | 0 | 15 | 0 | 20 | 0 | 25 | ns |

Shaded area contains preliminary information.

## Switching Waveforms

Read Cycle No. 1


## Notes:

3. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5 V , input pulse levels of 0 to 3.0 V , and output loading of the specified $\mathrm{I}_{\mathrm{OL}} / \mathrm{IOH}_{\mathrm{OH}}$ and $30-\mathrm{pF}$ load capacitance.
4. $t_{H Z C S}$ and $t_{H Z W E}$ are specified with $C_{L}=5 \mathrm{pF}$ as in part (b) of AC Test Loads and Waveforms. Transition is measured $\pm 500 \mathrm{mV}$ from steady state voltage.
5. The internal write time of the memory is defined by the overlap of CS LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
6. WE is HIGH for read cycle.
7. Device is continuously selected, $\overline{\mathrm{CS}}=\mathrm{V}_{\mathrm{IL}}$.

Switching Waveforms (continued)


Write Cycle No. 1 ( $\overline{\mathrm{WE}}$ Controlled) ${ }^{[5]}$


Write Cycle No. 2 (CS Controlled) ${ }^{[5,9]}$


## Notes:

8. Address valid prior to or coincident with $\overline{\mathrm{CS}}$ transition LOW.
9. If CS goes HIGH simultaneously with WE HIGH, the output remains in a high-impedance state.

## Truth Table

| $\overline{\mathbf{C S}}$ | WE | Input/Output | Mode |
| :---: | :---: | :--- | :--- |
| H | X | High Z | Deselect/Power-Down |
| L | H | Data Out | Read |
| L | L | Data In | Write |

Ordering Information

| Speed | Ordering Code | Package <br> Name | Package Type | Operating <br> Range |
| :---: | :--- | :---: | :--- | :--- |
| 20 | CYM1441PZ-20C | PZ04 | 60-Pin ZIP Module | Commercial |
| 25 | CYM1441PZ-25C | PZ04 | 60-Pin ZIP Module | Commercial |
| 35 | CYM1441PZ-35C | PZ04 | 60-Pin ZIP Module | Commercial |
| 45 | CYM1441PZ-45C | PZ04 | 60-Pin ZIP Module | Commercial |

Shaded area contains preliminary information.

## Package Diagrams

## 60-Pin ZIP Module PZ04



DIMENSIONS IN INCHES
MIN.
MAX.

| Document Title: CYM1441 256K x 8 Static RAM Module |  |  |  |  |
| :---: | :---: | :---: | :---: | :--- |
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